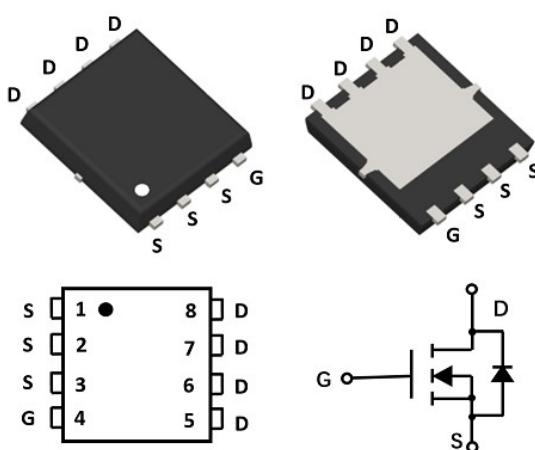


N-Channel Enhancement Mode Field Effect Transistor

PDFN5060-8L



Product Summary

- V_{DS} 60V
- I_D 70A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <7.5 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <9.5 mohm
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions
- Industrial and Motor Drive application

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current (Silicon limited)	$T_c=25^\circ C$	I_D	70	A
	$T_c=100^\circ C$		44	
Pulsed Drain Current ^A		I_{DM}	210	A
Avalanche energy ^B		E_{AS}	162	mJ
Total Power Dissipation ^C	$T_c=25^\circ C$	P_D	70	W
	$T_c=100^\circ C$		28	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$t \leq 10S$	$R_{\theta JA}$	14	17	°C/W
Thermal Resistance Junction-to-Ambient ^D	Steady-State		40	55	
Thermal Resistance Junction-to-Case	Steady-State		1.3	1.8	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG70G06A	F1	YJG70G06A	5000	10000	100000	13" reel



YJG70G06A

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	$T_J=25^\circ\text{C}$		1	μA
			$T_J=55^\circ\text{C}$		5	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.2	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= 10\text{V}, I_{\text{D}}=20\text{A}$		5.3	7.5	$\text{m}\Omega$
		$V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=10\text{A}$		6.9	9.5	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$		0.85	1.3	V
Maximum Body-Diode Continuous Current	I_{S}				70	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=35\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		2000		pF
Output Capacitance	C_{oss}			390		
Reverse Transfer Capacitance	C_{rss}			13		
Gate Resistance	R_g	$f=1\text{MHz}, \text{Open drain}$		1.6		Ω
Switching Parameters						
Total Gate Charge	$Q_g(10\text{V})$	$V_{\text{DS}}=30\text{V}, I_{\text{D}}=20\text{A}$		34		nC
Total Gate Charge	$Q_g(4.5\text{V})$			15.8		
Gate-Source Charge	Q_{gs}			7.8		
Gate-Drain Charge	Q_{gd}			5.2		
Reverse Recovery Charge	Q_{rr}	$I_F=20\text{A}, \text{di/dt}=200\text{A/us}$		36		ns
Reverse Recovery Time	t_{rr}			27		
Turn-on Delay Time	$t_{\text{D(on)}}$			10		
Turn-on Rise Time	t_r	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=30\text{V}, I_{\text{D}}=12\text{A}$ $R_{\text{GEN}}=3\Omega$		36		ns
Turn-off Delay Time	$t_{\text{D(off)}}$			30		
Turn-off fall Time	t_f			57		

A. Repetitive rating; pulse width limited by max. junction temperature.

B. $V_{\text{DD}}=50\text{V}$, $R_g=25\Omega$, $L=1\text{mH}$, $I_{\text{AS}}=18\text{A}$.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{GJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\text{GJA}} \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.



■ Typical Performance Characteristics

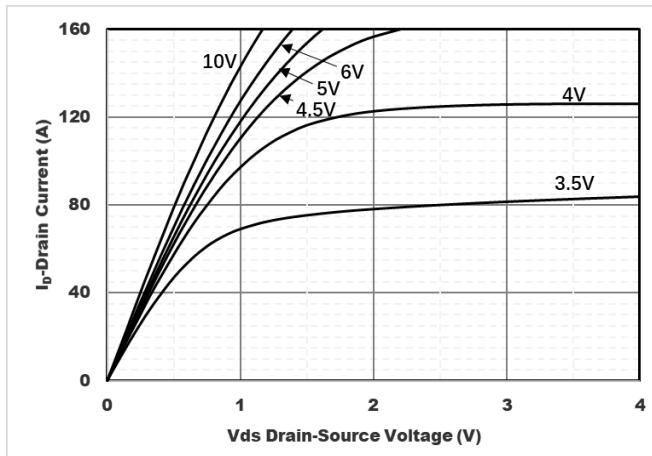


Figure1. Output Characteristics

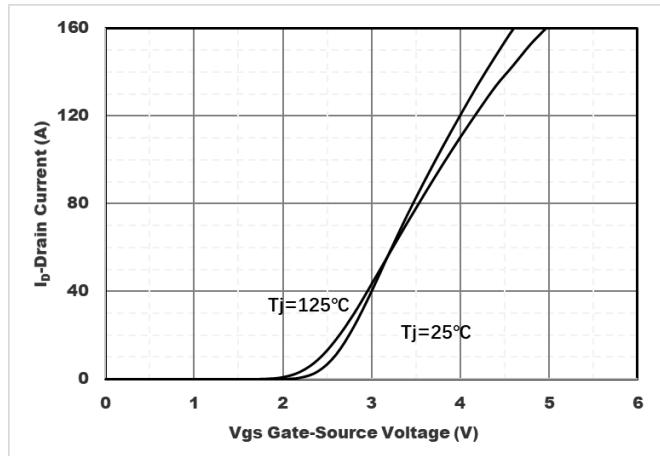


Figure2. Transfer Characteristics

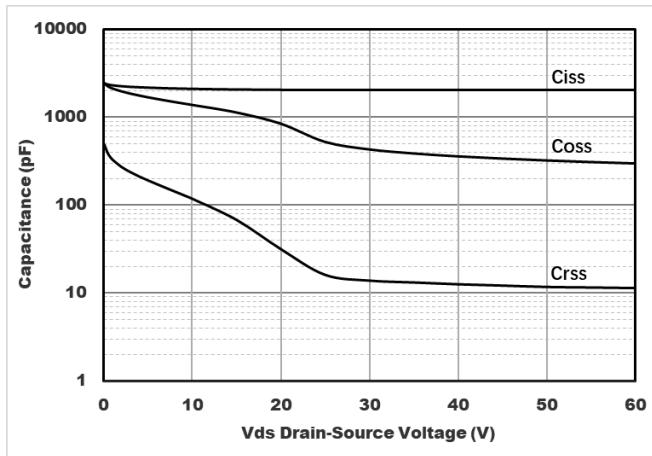


Figure3. Capacitance Characteristics

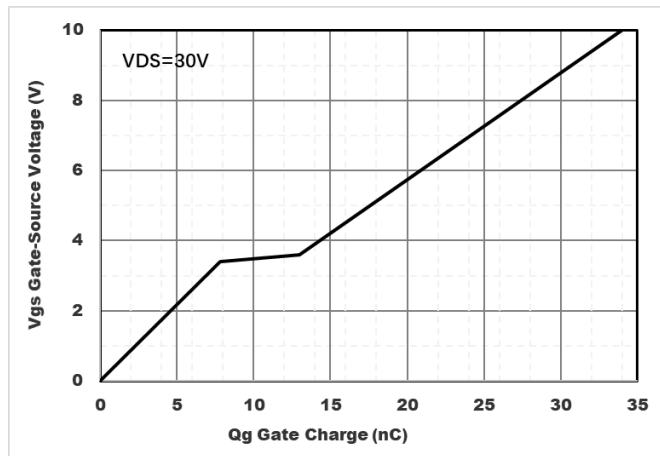


Figure4. Gate Charge

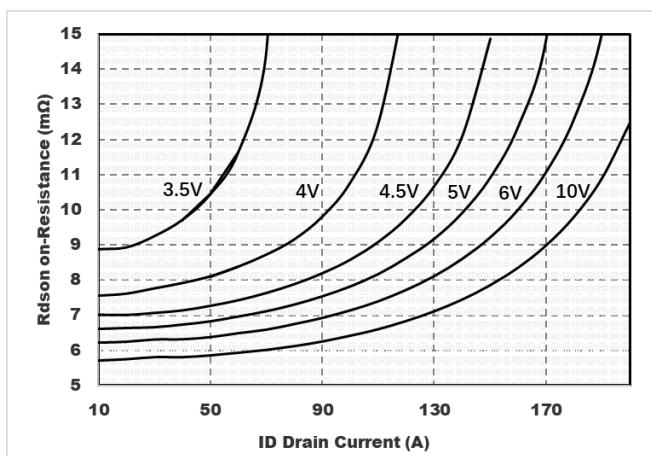


Figure5. Drain-Source on Resistance

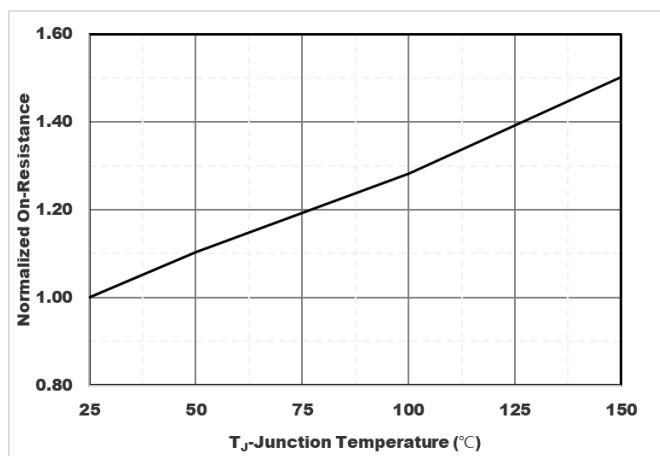


Figure6. Normalized On-Resistance

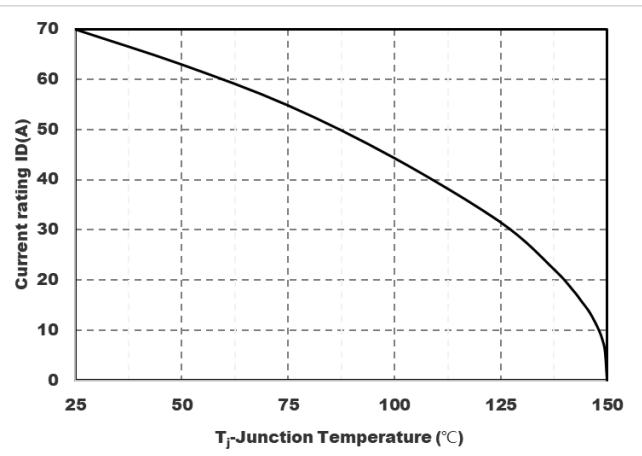


Figure7. Drain current

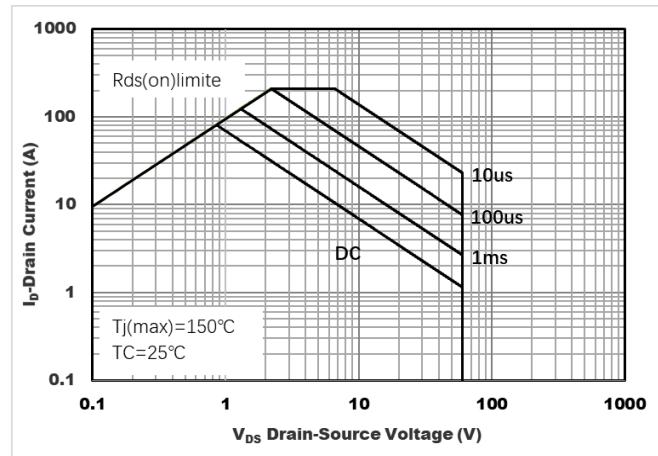


Figure8. Safe Operation Area

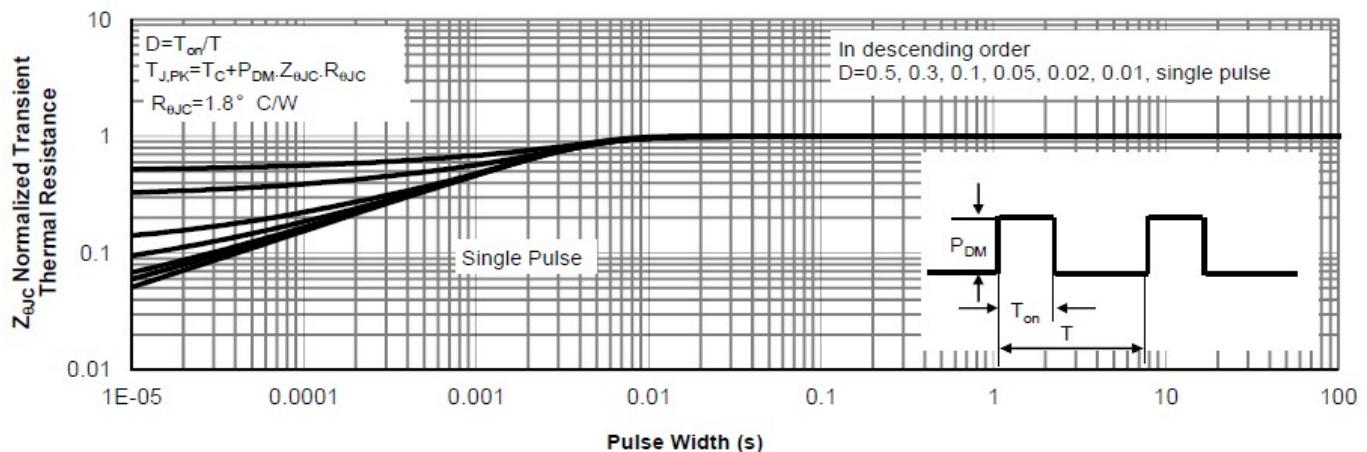
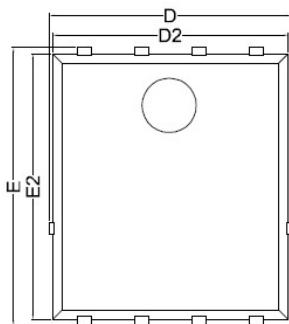
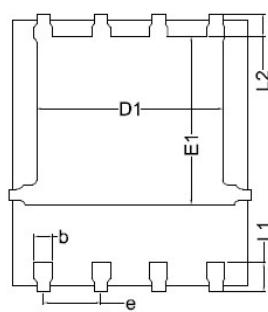
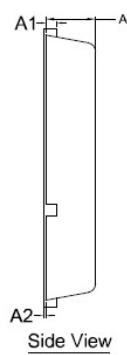
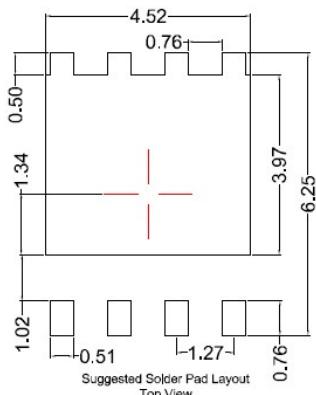


Figure8. Normalized Maximum Transient Thermal Impedance



■ PDFN5060-8L Package information

Top View
正面视图Bottom View
背面视图Side View
侧面视图Suggested Soldier Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1		0.254 BSC	
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2		0.50 BSC	
b	0.31	0.41	0.51
e		1.27 BSC	

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.10\text{mm}$.
3. The pad layout is for reference purposes only.



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